4-Bit Magnitude Comparator

The MC14585B 4–Bit Magnitude Comparator is constructed with complementary MOS (CMOS) enhancement mode devices. The circuit has eight comparing inputs (A3, B3, A2, B2, A1, B1, A0, B0), three cascading inputs (A < B, A = B, and A > B), and three outputs (A < B, A = B, and A > B). This device compares two 4–bit words (A and B) and determines whether they are "less than", "equal to", or "greater than" by a high level on the appropriate output. For words greater than 4–bits, units can be cascaded by connecting outputs (A > B), (A < B), and (A = B) to the corresponding inputs of the next significant comparator. Inputs (A < B), (A = B), and (A > B) on the least significant (first) comparator are connected to a low, a high, and a low, respectively.

Applications include logic in CPU's, correction and/or detection of instrumentation conditions, comparator in testers, converters, and controls.

Features

- Diode Protection on All Inputs
- Expandable
- Applicable to Binary or 8421–BCD Code
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load over the Rated Temperature Range
- Can be Cascaded See Figure 3
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to VSS

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	V _{DD}	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V _{in} , V _{out}	-0.5 to V _{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I _{in} , I _{out}	±10	mA
Power Dissipation per Package (Note 1)	P _D	500	mW
Ambient Temperature Range	T _A	-55 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Lead Temperature (8–Second Soldering)	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Temperature Derating: Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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MARKING DIAGRAMS



PDIP-16 P SUFFIX CASE 648 

SOIC-16 D SUFFIX CASE 751B

16 ______ 14585BG _o AWLYWW



SOEIAJ-16 F SUFFIX CASE 966 A = Assembly Location

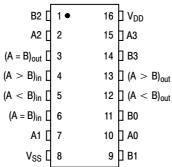
WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

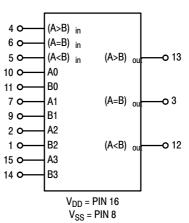
Device	Package	Shipping [†]
MC14585BCP	PDIP-16	25 Units / Rail
MC14585BCPG	PDIP-16 (Pb-Free)	25 Units / Rail
MC14585BD	SOIC-16	48 Units / Rail
MC14585BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14585BDR2	SOIC-16	2500/Tape & Reel
MC14585BDR2G	SOIC-16 (Pb-Free)	2500/Tape & Reel
MC14585BFEL	SOEIAJ-16	2000/Tape & Reel
MC14585BFELG	SOEIAJ-16 (Pb-Free)	2000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PIN ASSIGNMENT



BLOCK DIAGRAM



TRUTH TABLE (x = Don't Care)

Inputs					- 0					
	Comp	aring		Cascading			Outputs			
A3, B3	A2, B2	A1, B1	A0, B0	A < B	A = B	A > B	A < B	A = B	A > B	
A3 > B3	Х	Х	Х	Х	X	Х	0	0	1	
A3 = B3	A2 > B2	Х	Х	X 💨	X	Х	0	0	1	
A3 = B3	A2 = B2	A1 > B1	Х	X	Х	X	0	0	1	
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	X	0	0	1	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	0	Х	0	0	1	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	0	1	х	0	1	0	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	0	х	1	0	0	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	1	1	х	1	1	0	
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	х	Х	1	0	0	
A3 = B3	A2 = B2	A1 < B1	х	х	х	х	1	0	0	
A3 = B3	A2 < B2	X	Х	х	х	х	1	0	0	
A3 < B3	Х	х	Х	х	х	х	1	0	0	

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

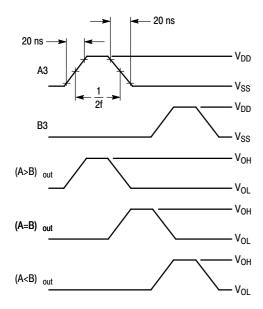
			- 5	5°C		25°C		125	5°C	
Characteristic	Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage "0" Level $V_{in} = V_{DD}$ or 0	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or V_{DD} "1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage "0" Level $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$	V _{IL}	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
"1" Level $(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	V _{IH}	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	_ _ _	Vdc
	Іон	5.0 5.0 10 15	- 3.0 - 0.64 - 1.6 - 4.2	1 1 1	- 2.4 - 0.51 - 1.3 - 3.4	- 4.2 - 0.88 - 2.25 - 8.8		- 1.7 - 0.36 - 0.9 - 2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ Sink $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	1 1 1	0.36 0.9 2.4	- - -	mAdc
Input Current	I _{in}	15	-	±0.1	~O\	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V _{in} = 0)	C _{in}	-	-	-	U -	5.0	7.5	_	-	pF
Quiescent Current (Per Package)	I _{DD}	5.0 10 15) =	5.0 10 20	- - -	0.005 0.010 0.015	5.0 10 20	- - -	150 300 600	μAdc
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching)	IT.	5.0 10 15			$I_{T} = (1$).6 μΑ/kHz) f l.2 μΑ/kHz) f l.8 μΑ/kHz) f	+ I _{DD} + I _{DD}			μAdc

- Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF: I_T(C_L) = I_T(50 pF) + (C_L 50) Vfk where: I_T is in μA (per package), C_L in pF, V = (V_{DD} V_{SS}) in volts, f in kHz is input frequency, and k = 0.001.

SWITCHING CHARACTERISTICS (Note 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$)

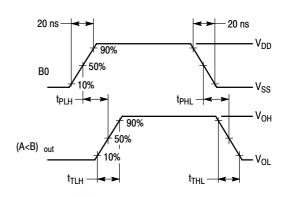
· · · · · · · · · · · · · · · · · · ·	, ,					
Characteristic	Symbol	V _{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time t_{TLH} , t_{THL} = (1.5 ns/pF) C_L + 25 ns t_{TLH} , t_{THL} = (0.75 ns/pF) C_L + 12.5 ns t_{TLH} , t_{THL} = (0.55 ns/pF) C_L + 9.5 ns	t _{TLH} , t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Turn-On, Turn-Off Delay Time t _{PLH} , t _{PHL} = (1.7 ns/pF) C _L + 345 ns t _{PLH} , t _{PHL} = (0.66 ns/pF) C _L + 147 ns t _{PLH} , t _{PHL} = (0.5 ns/pF) C _L + 105 ns	t _{PLH} , t _{PHL}	5.0 10 15	- - -	430 180 130	860 360 260	ns

- 5. The formulas given are for the typical characteristics only at 25°C.
 6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



Inputs (A>B) and (A=B) high, and inputs B2, A2, B1, A1, B0, A0 and (A<B) low. f in respect to a system clock.

Figure 1. Dynamic Power Dissipation **Signal Waveforms**



ngu, and inputs B3, A3, land inputs B3, land inpu Inputs (A>B) and (A=B) high, and inputs B3, A3, B2, A2, B1, A1, A0, and (A<B) low.

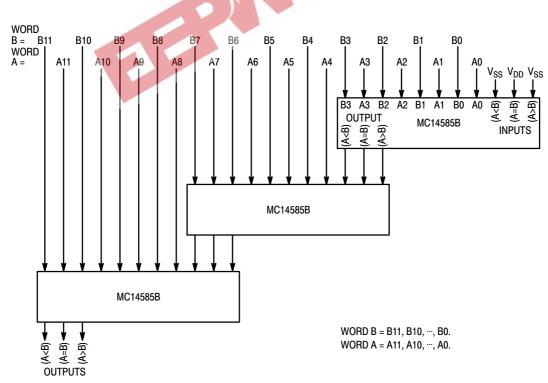
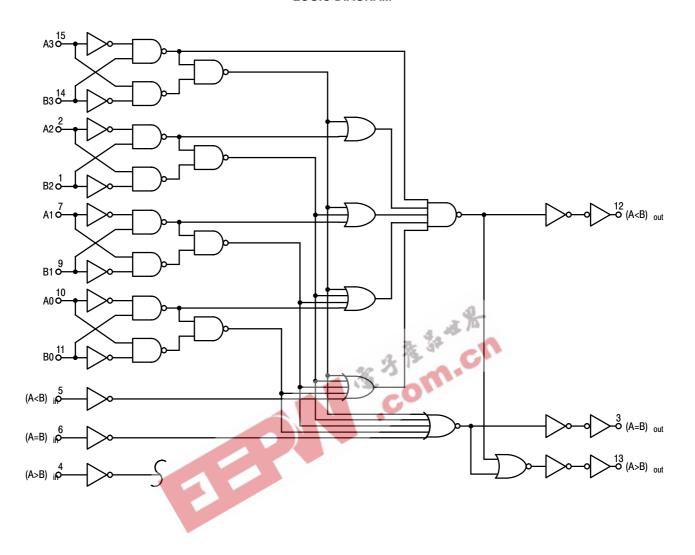


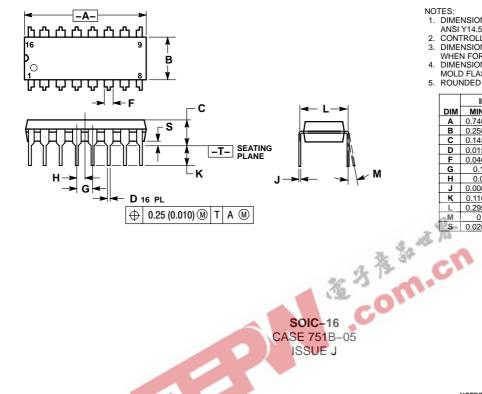
Figure 3. Cascading Comparators

LOGIC DIAGRAM



PACKAGE DIMENSIONS

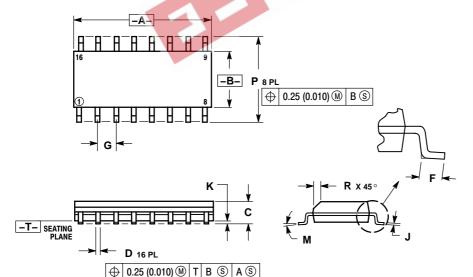
PDIP-16 CASE 648-08 **ISSUE T**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER

- DIMENSIONING AND TOLERANCING PANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

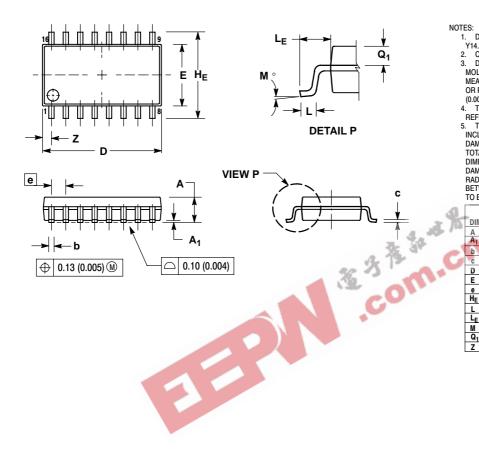
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MIN MAX		MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

SOEIAJ-16 CASE 966-01 ISSUE A



- 1. DIMEINO. Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE, MOLD FLASH
 ORD ROCKET BLOCK OF THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q_1	0.70	0.90	0.028	0.035
Z		0.78		0.031

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